

CMOS Hex Buffer

High-Voltage Types (20-Volt Rating)

3-State Non-Inverting Type

■ CD4503B is a hex noninverting buffer with 3-state outputs having high sink- and source-current capability. Two disable controls are provided, one of which controls four buffers and the other controls the remaining two buffers. The CD4503B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- 1 TTL-load output drive capability
- 2 output-disable controls
- 3-state outputs
- Pin compatible with industry types MM80C97, MC14503, and 340097
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- 3-state hex buffer for interfacing IC's with data buses
- CMOS to TTL hex buffer

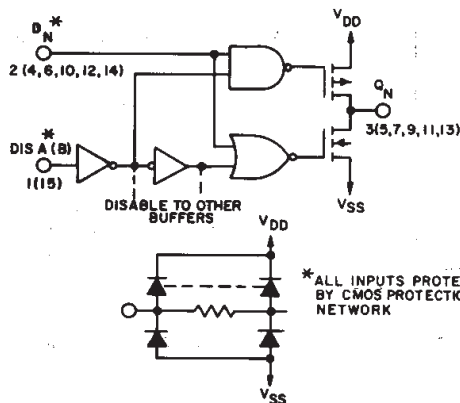
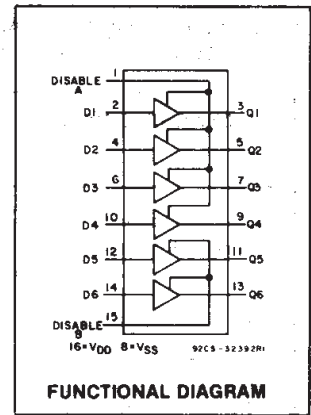
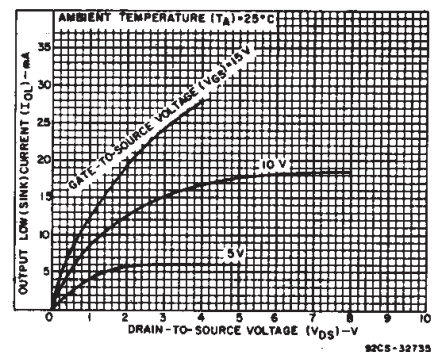
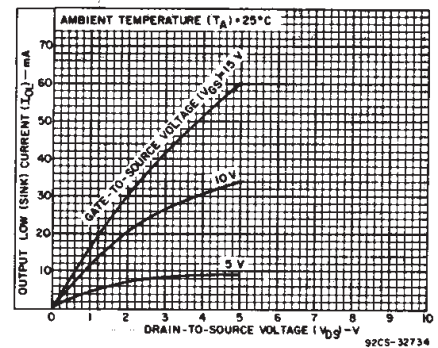


Fig. 1—Logic diagram of 1 to 6 identical buffers.



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal) -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to $V_{DD} + 0.5V$

DC INPUT CURRENT, ANY ONE INPUT $\pm 10\text{mA}$

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$ 500mW

For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$ Derate Linearity at 12mW/ $^\circ\text{C}$ to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

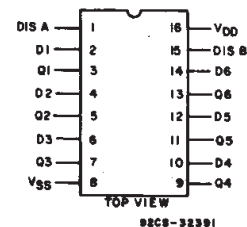
FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$ 100mW

OPERATING-TEMPERATURE RANGE (T_A) -55°C to $+125^\circ\text{C}$

STORAGE TEMPERATURE RANGE (T_{stg}) -65°C to $+150^\circ\text{C}$

LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79mm) from case for 10s max $+265^\circ\text{C}$



TERMINAL ASSIGNMENT

CD4503B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	—	0,5	5	1	1	30	30	—	0.02	1	μA
	—	0,10	10	2	2	60	60	—	0.02	2	
	—	0,15	15	4	4	120	120	—	0.02	4	μA
	—	0,20	20	20	20	600	600	—	0.04	20	
Output Low (Sink) Current, I _{OL} Min.	0.4	0	5	2.6	2.5	1.4	1.3	2.1	2.3	—	mA
	0.5	0	10	6.5	6.4	3.9	3.8	5.5	6.2	—	
	1.5	0	15	19.2	18.9	11.4	11.2	16.1	23	—	
Output High (Source) Current, I _{OH} Min.	4.6	5	5	-1.2	-1.16	-0.7	-0.7	-1.02	-1.9	—	mA
	2.5	5	5	-5.8	-5.7	-3.4	-3	-4.8	-6.1	—	
	9.5	10	10	-3.1	-3	-1.9	-1.8	-2.6	-3.7	—	
	13.5	15	15	-8.2	-8	-4.9	-4.8	-6.8	-14.1	—	mA
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	V
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	V
Input Low Voltage, V _{IL} Max.	0.5, 4.5	—	5	1.5				—	—	1.5	
	1,9	—	10	3				—	—	3	
	1.5, 13.5	—	15	4				—	—	4	V
Input High Voltage, V _{IH} Min.	0.5, 4.5	—	5	3.5				3.5	—	—	
	1,9	—	10	7				7	—	—	
	1.5, 13.5	—	15	11				11	—	—	μA
Input Current I _{IN} Max.	—	0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	
3-State Output Leakage Current, I _{OUT} Max.	0,18	0,18	18	±0.4	±0.4	±12	±12	—	±10 ⁻⁴	±0.4	

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For T _A = Full Package-Temperature Range)	3	18	V

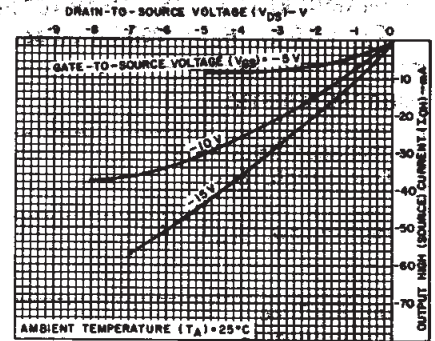


Fig. 4—Typical p-channel output high (source) current characteristics.

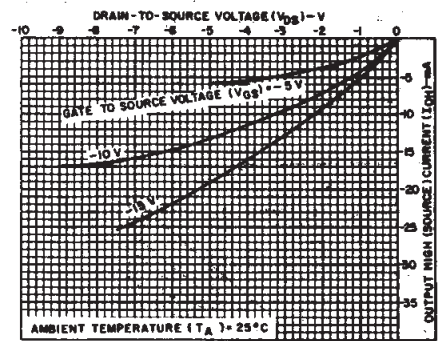


Fig. 5—Minimum p-channel output high (source) current characteristics.

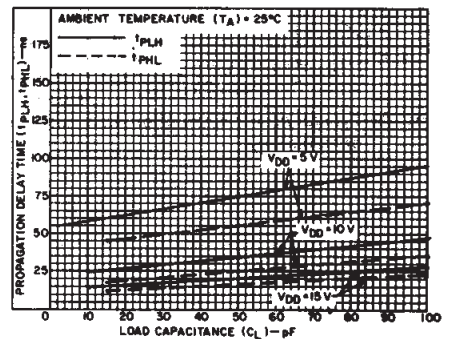


Fig. 6—Typical propagation delay time as a function of load capacitance.

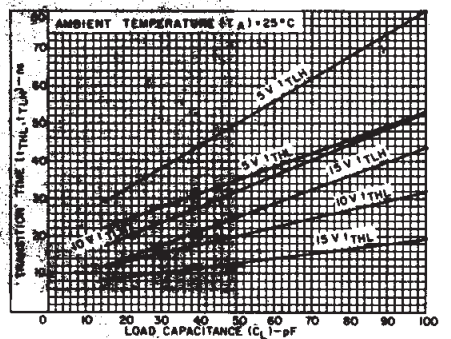


Fig. 7—Typical transition time as a function of load capacitance.

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

CD4503B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$; input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$ unless otherwise specified.

CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		Typ.	Max.	
Propagation Delay Time: Low-to-High, t_{PLH}	5	75	150	ns
	10	35	70	
	15	25	50	
High-to-Low, t_{PHL}	5	55	110	ns
	10	25	50	
	15	17	35	
Transition Time: Low-to-High, t_{TLH}	5	50	90	ns
	10	30	45	
	15	25	35	
High-to-Low, t_{THL}	5	35	70	ns
	10	20	40	
	15	13	25	
3-State Propagation Delay Time: $R_L = 1\text{ k}\Omega$ t_{PHZ}, t_{PZH}	5	70	140	ns
	10	30	60	
	15	25	50	
t_{PZL}, t_{PLZ}	5	90	180	ns
	10	40	80	
	15	35	70	

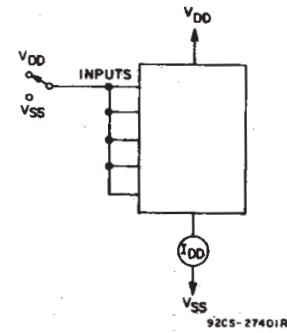


Fig. 10—Quiescent device current test circuit.

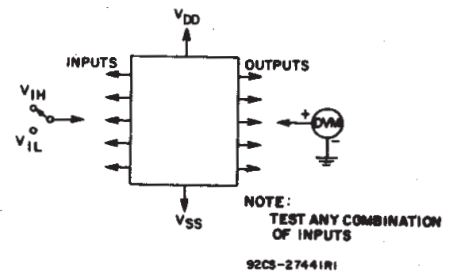


Fig. 11—Input voltage test circuit.

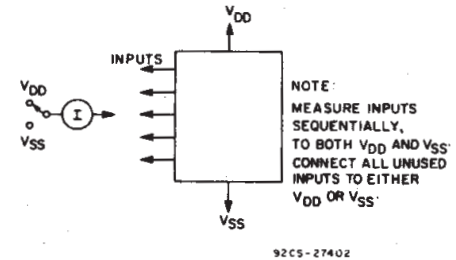


Fig. 12—Input current test circuit.

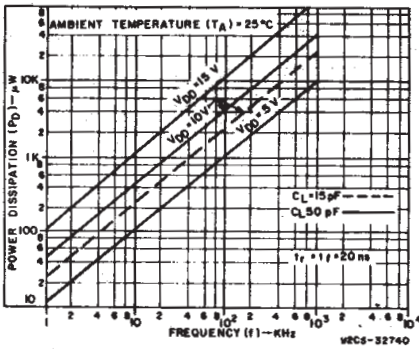


Fig. 8—Typical power dissipation as a function of frequency.

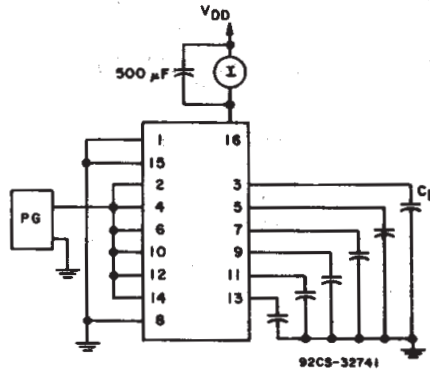
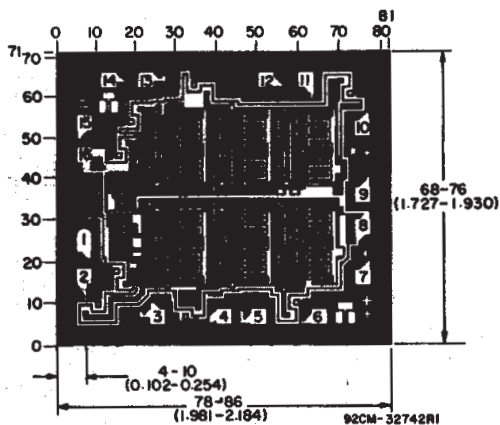


Fig. 9—Dynamic power dissipation test circuit.



Dimensions and pad layout for CD4503BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.

Texas Instruments

<http://www.ti.com>

This file is the datasheet for the following electronic components:

CD4503 - <http://www.ti.com/product/cd4503?HQS=TI-null-null-dscatalog-df-pf-null-ww>



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.